



DMP2070U

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
	$44m\Omega$ @ $V_{GS} = -4.5V$	-4.6A
-20V	57mΩ @ V _{GS} = -2.5V	-4A
	74mΩ @ V _{GS} = -1.8V	-3.5A

Features

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Loadswitch

Mechanical Data

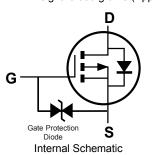
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

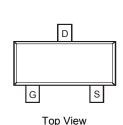




SOT23

Top View





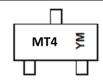
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2070U-7	SOT23	3,000 / Tape & Reel
DMP2070U-13	SOT23	10,000 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



MT4 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	Н		J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-20	V	
Gate-Source Voltage	V_{GSS}	±8	V	
Continuous Drain Current (Note 7) V _{GS} = -4.5V	I _D	-4.6 -3.7	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-20	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	-1.9	Α	
Avalanche Current, L = 0.1mH (Note 8)	I _{AS}	-14	Α	
Avalanche Energy, L = 0.1mH (Note 8)		E _{AS}	10	mJ

Thermal Characteristics

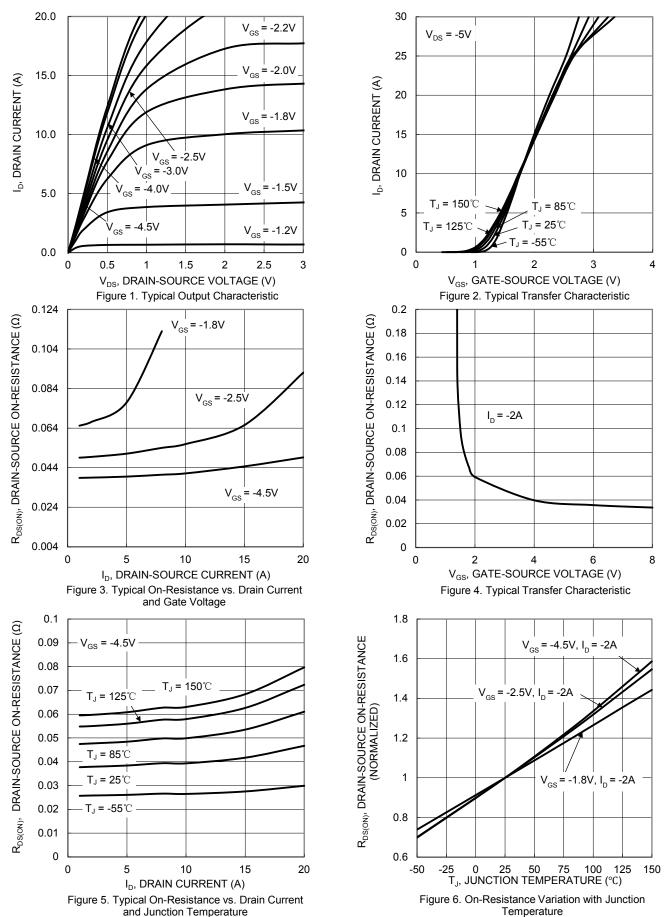
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P _D	0.83	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	153	°C/W
Total Power Dissipation (Note 6)		P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	90	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	15.1	C/VV
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
	Зуппоп	IVIIII	Тур	IVIAX	Ollit	rest condition	
OFF CHARACTERISTICS (Note 9)	1		Т	ı		1	
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V$, $I_D = -1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-0.45	_	-0.95	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
		_	37	44		V _{GS} = -4.5V, I _D = -2A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	48	57	mΩ	V _{GS} = -2.5V, I _D = -2A	
		_	65	74		V _{GS} = -1.8V, I _D = -2A	
Diode Forward Voltage	V _{SD}	_	-0.7	-1.1	V	V _{GS} = 0V, I _S = -2.1A	
DYNAMIC CHARACTERISTICS (Note 10)	•		•				
Input Capacitance	C _{iss}	_	118	_			
Output Capacitance	Coss	_	79	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	11	_		- 1101112	
Gate Resistance	R _G	_	459	_	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz	
Total Gate Charge (V _{GS} = -8V)	Qg	_	8.2	_			
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	17.8	_	nC	.,	
Gate-Source Charge	Q _{gs}	_	1.4	_	IIC	$V_{DD} = -10V, I_D = -2A$	
Gate-Drain Charge	Q _{gd}	_	1.2	_	1		
Turn-On Delay Time	t _{D(ON)}	_	115	_			
Turn-On Rise Time	t _R	_	304	_	1	$V_{GS} = -4.5V, V_{DD} = -10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	780	_	ns	$R_G = 1\Omega$, $I_D = -2A$	
Turn-Off Fall Time	t _F		666	_	1		

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- Device mounted on FR-4 PC board, with minimum recommended pad rayout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







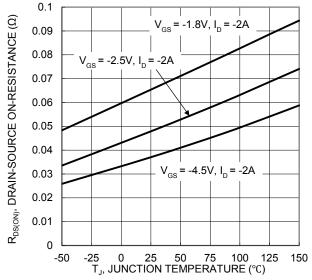


Figure 7. On-Resistance Variation with Junction Temperature

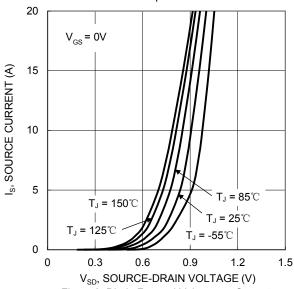


Figure 9. Diode Forward Voltage vs. Current 10 8 6 $V_{GS}(V)$ 4 $V_{DS} = -10V, I_{D} = -2A$ 2 0 3 0 9 12 15 18 Q_g (nC)

Figure 11. Gate Charge

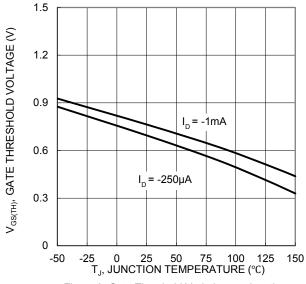
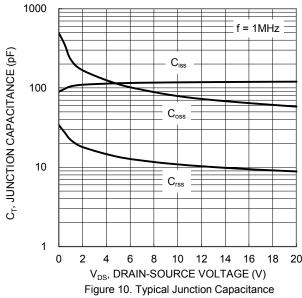
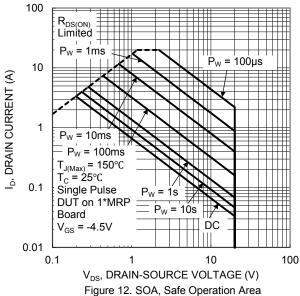


Figure 8. Gate Threshold Variation vs. Junction Temperature





April 2021



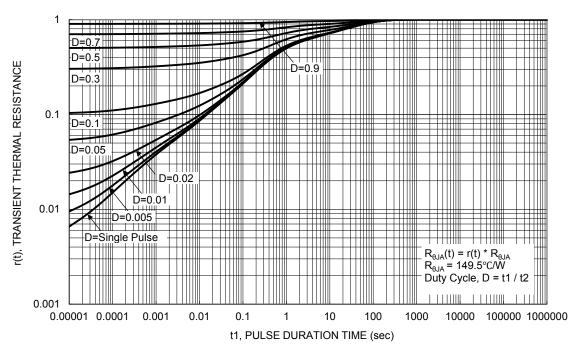


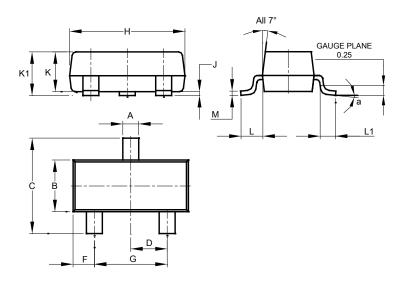
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

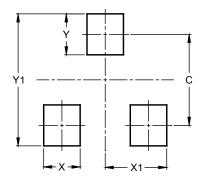


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)			
С	2.0			
Х	0.8			
X1	1.35			
Υ	0.9			
Y1	2.9			



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